

MMSF3P02HDR2G

MMSF3P02HDR2G Information



For Reference Only

Part Number MMSF3P02HDR2G Manufacturer ON Semiconductor

Category Discrete Semiconductor Products

Transistors - FETs, MOSFETs - Single

Description MOSFET P-CH 20V 5.6A 8-SOIC **Package** 8-SOIC (0.154", 3.90mm Width)

For the pricing/inventory/lead time, please contact

us

Website: https://www.heisener.com E-mail: salesdept@heisener.com



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MMSF3P02HDR2G Specifications

Manufacturer Part Number MMSF3P02HDR2G Manufacturer ON Semiconductor Category Discrete Semiconductor Products Transistors - FETs, MOSFETs - Single Package 8-SOIC (0.154", 3.90mm Width) Series - FET Type P-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 20V Current - Continuous Drain (Id) @ 25°C 5.6A (Ta) Drive Voltage (Max Rds On, Min Rds On) 4.5V, 10V Vgs(th) (Max) @ Id 2V @ 250µA Gate Charge (Qg) (Max) @ Vgs 46nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 1400pF @ 16V Vgs (Max) ± 20V FET Feature - Power Dissipation (Max) 2.5W (Ta) Rds On (Max) @ Id, Vgs 75 mOhm @ 3A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package 8-SOIC Package / Case 8-SOIC (0.154", 3.90mm Width)		
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FET TypeP-ChannelTechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)20VCurrent - Continuous Drain (Id) @ 25°C5.6A (Ta)Drive Voltage (Max Rds On, Min Rds On)4.5V, 10VVgs(th) (Max) @ Id2V @ 250μAGate Charge (Qg) (Max) @ Vgs46nC @ 10VInput Capacitance (Ciss) (Max) @ Vds1400pF @ 16VVgs (Max)±20VFET Feature-Power Dissipation (Max)2.5W (Ta)Rds On (Max) @ Id, Vgs75 mOhm @ 3A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeSurface MountSupplier Device Package8-SOICPackage / Case8-SOIC (0.154", 3.90mm Width)	Package	8-SOIC (0.154", 3.90mm Width)
TechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)20VCurrent - Continuous Drain (Id) @ 25°C5.6A (Ta)Drive Voltage (Max Rds On, Min Rds On)4.5V, 10VVgs(th) (Max) @ Id2V @ 250μAGate Charge (Qg) (Max) @ Vgs46nC @ 10VInput Capacitance (Ciss) (Max) @ Vds1400pF @ 16VVgs (Max)±20VFET Feature-Power Dissipation (Max)2.5W (Ta)Rds On (Max) @ Id, Vgs75 mOhm @ 3A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeSurface MountSupplier Device Package8-SOICPackage / Case8-SOIC (0.154", 3.90mm Width)	Series	-
Drain to Source Voltage (Vdss)20VCurrent - Continuous Drain (Id) @ 25°C5.6A (Ta)Drive Voltage (Max Rds On, Min Rds On)4.5V, 10VVgs(th) (Max) @ Id2V @ 250μAGate Charge (Qg) (Max) @ Vgs46nC @ 10VInput Capacitance (Ciss) (Max) @ Vds1400pF @ 16VVgs (Max)±20VFET Feature-Power Dissipation (Max)2.5W (Ta)Rds On (Max) @ Id, Vgs75 mOhm @ 3A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeSurface MountSupplier Device Package8-SOICPackage / Case8-SOIC (0.154", 3.90mm Width)	FET Type	P-Channel
Current - Continuous Drain (Id) @ 25°C Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id Cate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs 75 mOhm @ 3A, 10V Operating Temperature Supplier Device Package Package / Case 5.6A (Ta) 5.6A (Technology	MOSFET (Metal Oxide)
Drive Voltage (Max Rds On, Min Rds On)4.5V, 10VVgs(th) (Max) @ Id2V @ 250μAGate Charge (Qg) (Max) @ Vgs46nC @ 10VInput Capacitance (Ciss) (Max) @ Vds1400pF @ 16VVgs (Max)±20VFET Feature-Power Dissipation (Max)2.5W (Ta)Rds On (Max) @ Id, Vgs75 mOhm @ 3A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeSurface MountSupplier Device Package8-SOICPackage / Case8-SOIC (0.154", 3.90mm Width)	Drain to Source Voltage (Vdss)	20V
Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package Package / Case 8-SOIC (0.154", 3.90mm Width)	Current - Continuous Drain (Id) @ 25°C	5.6A (Ta)
Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds 1400pF @ 16V Vgs (Max) ±20V FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs 75 mOhm @ 3A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package 8-SOIC Package / Case 8-SOIC (0.154", 3.90mm Width)	Drive Voltage (Max Rds On, Min Rds On)	4.5V, 10V
Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) E20V FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs 75 mOhm @ 3A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package 8-SOIC Package / Case 8-SOIC (0.154", 3.90mm Width)	Vgs(th) (Max) @ Id	2V @ 250μA
Vgs (Max)±20VFET Feature-Power Dissipation (Max)2.5W (Ta)Rds On (Max) @ Id, Vgs75 mOhm @ 3A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeSurface MountSupplier Device Package8-SOICPackage / Case8-SOIC (0.154", 3.90mm Width)	Gate Charge (Qg) (Max) @ Vgs	46nC @ 10V
FET Feature - Power Dissipation (Max) 2.5W (Ta) Rds On (Max) @ Id, Vgs 75 mOhm @ 3A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package 8-SOIC Package / Case 8-SOIC (0.154", 3.90mm Width)	Input Capacitance (Ciss) (Max) @ Vds	1400pF @ 16V
Power Dissipation (Max) Rds On (Max) @ Id, Vgs 75 mOhm @ 3A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package 8-SOIC Package / Case 8-SOIC (0.154", 3.90mm Width)	Vgs (Max)	±20V
Rds On (Max) @ Id, Vgs75 mOhm @ 3A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeSurface MountSupplier Device Package8-SOICPackage / Case8-SOIC (0.154", 3.90mm Width)	FET Feature	-
Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package 8-SOIC Package / Case 8-SOIC (0.154", 3.90mm Width)	Power Dissipation (Max)	2.5W (Ta)
Mounting Type Surface Mount Supplier Device Package 8-SOIC Package / Case 8-SOIC (0.154", 3.90mm Width)	Rds On (Max) @ Id, Vgs	75 mOhm @ 3A, 10V
Supplier Device Package 8-SOIC Package / Case 8-SOIC (0.154", 3.90mm Width)	Operating Temperature	-55°C ~ 150°C (TJ)
Package / Case 8-SOIC (0.154", 3.90mm Width)	Mounting Type	Surface Mount
	Supplier Device Package	8-SOIC
Report errors?	Package / Case	8-SOIC (0.154", 3.90mm Width)
		Report errors?

MMSF3P02HDR2G Guarantees



Quality Guarantees

We provide 90 days warranty. *

If the items you received were not in perfect quality, we would be responsible for your refund or replacement, but the items must be returned in their original condition.



Service Guarantees

We guarantee 100% customer satisfaction.

Our experienced sales team and tech support team back our services to satisfy all our customers.

MMSF3P02HDR2G Payment Methods



















MMSF3P02HDR2G Shipping Methods













If you have any question about MMSF3P02HDR2G, please do not hesitate to contact us!

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